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Color Code:
Red – Plasma Etching
Blue – Advanced Devices

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US Patent Nr.	Title	Assignee	Filed	Date of Patent
6,540,885	Profile control of oxide trench features for dual damascene applications	Lam Research Corp.	3/28/01	4/1/03
6,541,320	Method to controllably form notched polysilicon gate structures	International Business Machines Corporation	8/10/01	4/1/03
6,541,322	Method for preventing gate depletion effects of MOS transistor	Macronix International Co. Ltd.	5/17/01	4/1/03
6,541,360	Bi-layer trim etch process to form integrated circuit gate structures	Advanced Micro Devices, Inc.	4/30/01	4/1/03
6,541,361	Plasma enhanced method for increasing silicon-containing photoresist selectivity	Lam Research Corporation	6/27/01	4/1/03
6,541,821	SOI device with source/drain extensions and adjacent shallow pockets	Advanced Micro Devices, Inc.	12/7/00	4/1/03
6,544,827	Metal-gate field effect transistor and method for manufacturing the same	NEC Corporation	7/2/01	4/8/03
6,544,887	Polycide etch process	Lam Research Corporation	3/31/00	4/8/03

6,544,896	Method for enhancing etching of TiSix	Applied Materials, Inc.	10/10/00	4/8/03
6,544,906	Annealing of high-k dielectric materials	Texas Instruments Incorporated	10/25/01	4/8/03
6,545,324	Dual metal gate transistors for CMOS process	Motorola, Inc.	5/20/00	4/8/03
6,545,753	Using scatterometry for etch end points for dual damascene process	Advanced Micro Devices, Inc.	6/27/01	4/8/03
6,547,977	Method for etching low k dielectrics	Applied Materials, Inc.	7/5/00	4/15/03
6,548,361	SOI MOSFET and method of fabrication	Advanced Micro Devices, Inc.	5/15/02	4/15/03
6,548,414	Method of plasma etching thin films of difficult to dry etch materials	Infineon Technologies AG	9/14/99	4/15/03
6,551,447	Inductive plasma reactor	Mattson Technology, Inc.	11/6/00	4/22/03
6,551,870	Method of fabricating ultra shallow junction CMOS transistors with nitride disposable spacer	Advanced Micro Devices, Inc.	10/10/00	4/22/03
6,551,874	Self-aligned STI process using nitride hard mask	Infineon Technologies, AG	6/22/01	4/22/03
6,551,886	Ultra-thin body SOI MOSFET and gate-last fabrication method	Advanced Micro Devices, Inc.	4/27/01	4/22/03
6,551,938	N2/H2 chemistry for dry development in top surface imaging technology	Taiwon Semiconductor Manufacturing Company	1/25/02	4/22/03
6,551,941	Method of forming a notched silicon-containing gate structure	Applied Materials, Inc.	2/22/01	4/22/03

6,552,296	Toroidal low-field reactive gas source	Applied Science and Technology, Inc.	9/17/01	4/22/03
6,553,332	Method for evaluating process chambers used for semiconductor manufacturing	Texas Instruments Incorporated	11/30/00	4/22/03
6,555,472	Method of producing a semiconductor device using feature trimming	Advanced Micro Devices, Inc.	3/21/01	4/29/03
6,555,482	Process for fabricating a MOS transistor having two gates, one of which is buried and corresponding transistor	STMicroelectronics S.A.	3/20/01	4/29/03
6,559,468	Molecular wire transistor (MWT)	Hewlett-Packard Development Company LP	10/26/00	5/6/03